

NDT02N60Z

N-Channel Power MOSFET 600 V, 8.0 Ω

Features

- 100% Avalanche Tested
- Extremely High dv/dt Capability
- Gate Charge Minimized
- Zener-protected
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	600	V
Gate-to-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current $R_{\theta JA}$ Steady State, $T_C = 25^\circ\text{C}$	I_D	0.3	A
Continuous Drain Current $R_{\theta JA}$ Steady State, $T_C = 100^\circ\text{C}$	I_D	0.21	A
Power Dissipation – $R_{\theta JA}$ Steady State, $T_C = 25^\circ\text{C}$	P_D	2.0	W
Pulsed Drain Current	I_{DM}	5	A
Continuous Source Current (Body Diode)	I_S	2.2	A
Single Pulse Drain-to-Source Avalanche Energy ($I_D = 1.4$ A)	EAS	38	mJ
Peak Diode Recovery (Note 1)	dV/dt	4.5	V/ns
Maximum Temperature for Soldering Leads	T_L	260	$^\circ\text{C}$
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $I_S < 2.2$ A, $di/dt \leq 200$ A/ μs , $V_{DD} \leq BV_{DSS}$, $T_J = +150^\circ\text{C}$

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction-to-Ambient Steady State NDT02N60Z (Note 2) NDT02N60Z (Note 3)	$R_{\theta JA}$	61 148	$^\circ\text{C/W}$

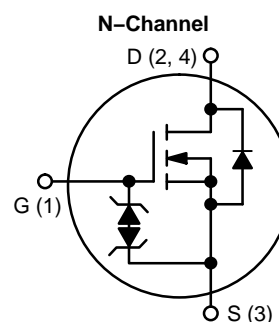
2. Surface mounted on FR4 board using 1" sq. pad size (Cu area = 1.127" sq. [2 oz] including traces)
3. Surface-mounted on FR4 board using minimum recommended pad size (Cu area = 0.026" sq. [2 oz]).



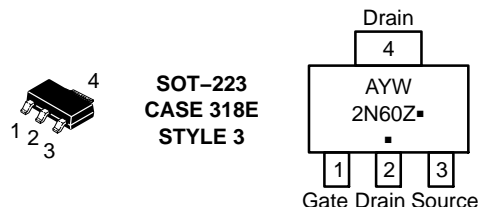
ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$
600 V	8.0 Ω @ 10 V



MARKING DIAGRAM



- A = Assembly Location
Y = Year
W = Work Week
2N60Z = Specific Device Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NDT02N60Z

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	600			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	Reference to 25°C, I _D = 1 mA		605		mV/°C
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	T _J = 25°C		1	μA
			T _J = 125°C		50	
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±20 V			±10	μA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 50 μA	3.0	3.9	4.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J	Reference to 25°C, I _D = 50 μA		10.2		mV/°C
Static Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 0.7 A		5.9	8.0	Ω
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 0.7 A		1.3		S

DYNAMIC CHARACTERISTICS

Input Capacitance (Note 5)	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		170		pF
Output Capacitance (Note 5)	C _{oss}			22		
Reverse Transfer Capacitance (Note 5)	C _{rss}			4.8		
Effective output capacitance, energy related (Note 7)	C _{o(er)}	V _{GS} = 0 V, V _{DS} = 0 to 480 V		7.8		
Effective output capacitance, time related (Note 8)	C _{o(tr)}	I _D = constant, V _{GS} = 0 V, V _{DS} = 0 to 480 V		12.4		
Total Gate Charge (Note 5)	Q _g	V _{DS} = 300 V, I _D = 1.6 A, V _{GS} = 10 V		7.4		nC
Gate-to-Source Charge (Note 5)	Q _{gs}			1.8		
Gate-to-Drain ("Miller") Charge (Note 5)	Q _{gd}			3.8		
Plateau Voltage	V _{GP}			6.4		V
Gate Resistance	R _g			11.5		Ω

RESISTIVE SWITCHING CHARACTERISTICS (Note 6)

Turn-on Delay Time	t _{d(on)}	V _{DD} = 300 V, I _D = 1.6 A, V _{GS} = 10 V, R _G = 0 Ω		10		ns
Rise Time	t _r			6		
Turn-off Delay Time	t _{d(off)}			14		
Fall Time	t _f			8		

SOURCE-DRAIN DIODE CHARACTERISTICS

Diode Forward Voltage	V _{SD}	I _S = 1.6 A, V _{GS} = 0 V	T _J = 25°C		0.9	1.2	V
			T _J = 100°C		0.8		
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, V _{DD} = 30 V, I _S = 1.6 A, dI/dt = 100 A/μs		230			ns
Charge Time	t _a			50			
Discharge Time	t _b			180			
Reverse Recovery Charge	Q _{rr}			495			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.

5. Guaranteed by design.

6. Switching characteristics are independent of operating junction temperatures.

7. C_{o(er)} is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}

8. C_{o(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}

TYPICAL CHARACTERISTICS

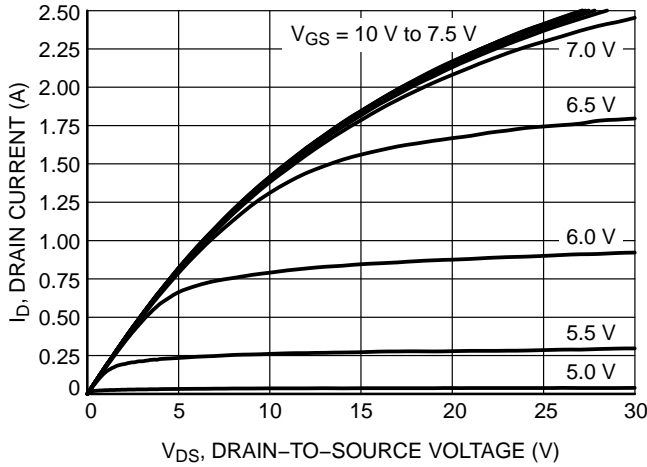


Figure 1. On-Region Characteristics

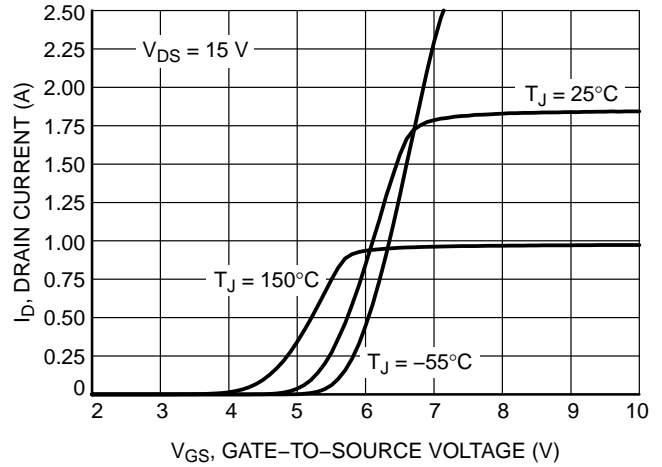


Figure 2. Transfer Characteristics

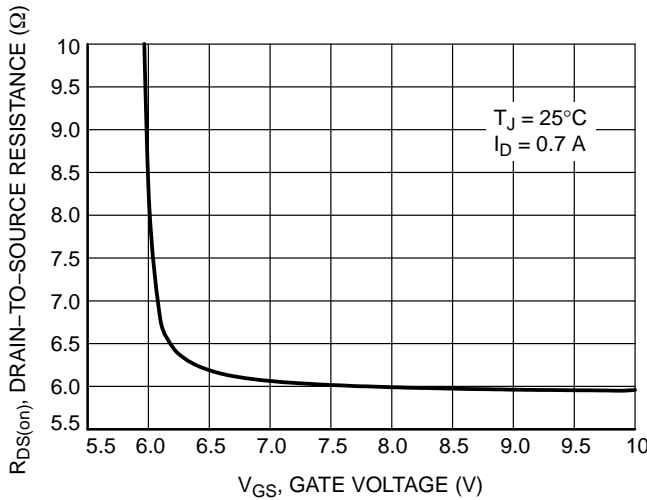


Figure 3. On-Resistance vs. Gate-to-Source Voltage

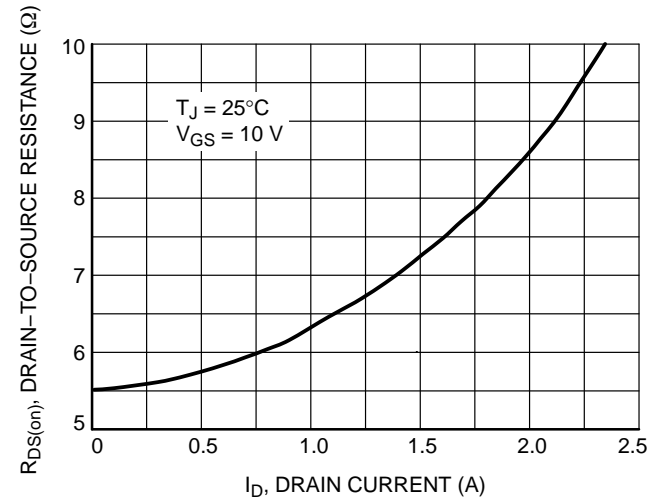


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

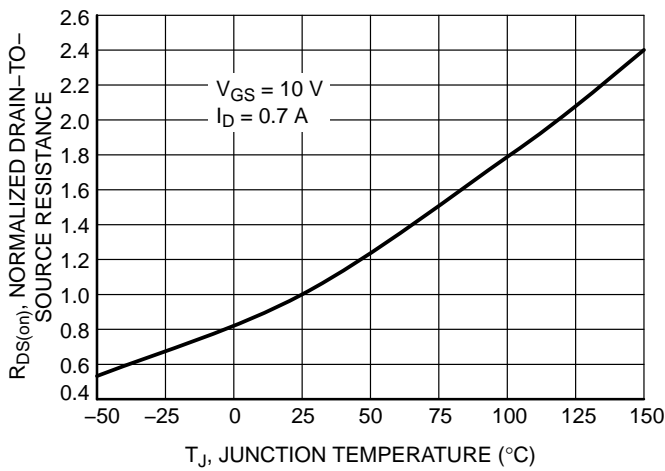


Figure 5. On-Resistance Variation with Temperature

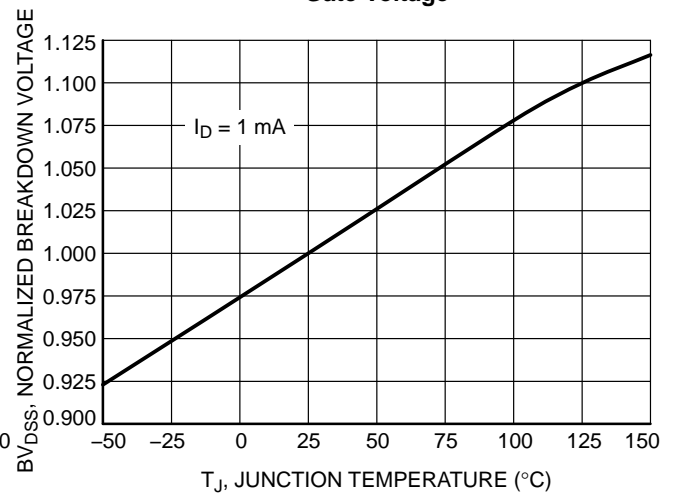


Figure 6. Breakdown Voltage Variation with Temperature

TYPICAL CHARACTERISTICS

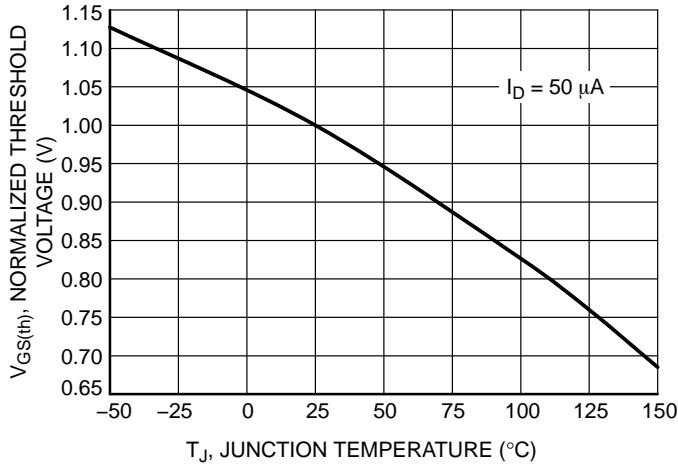


Figure 7. Threshold Voltage Variation with Temperature

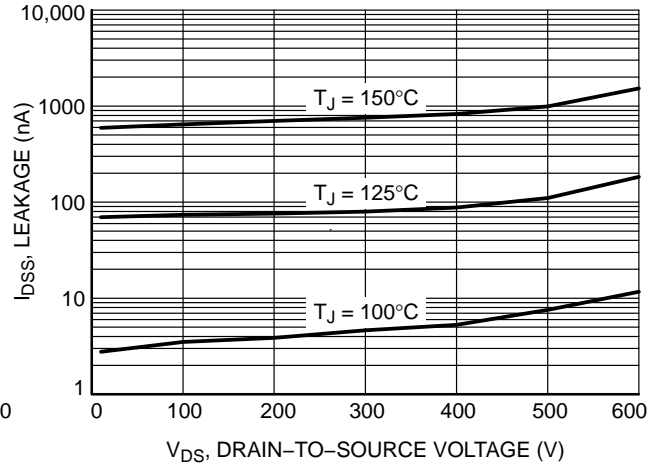


Figure 8. Drain-to-Source Leakage Current vs. Voltage

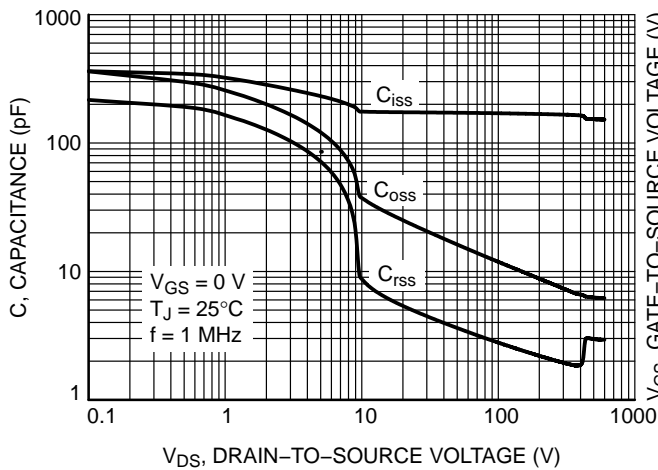


Figure 9. Capacitance Variation

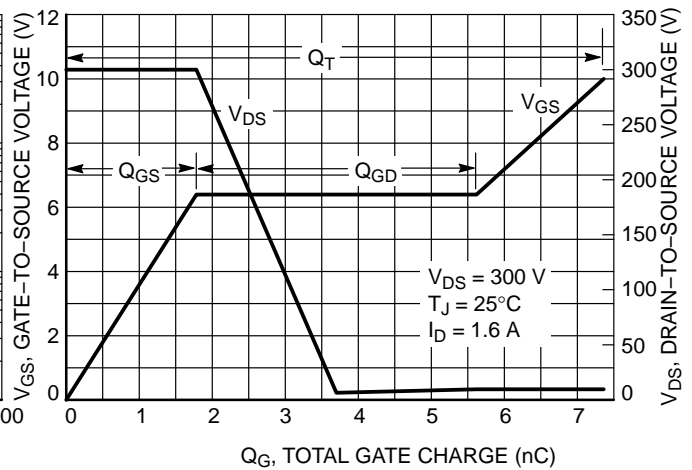


Figure 10. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

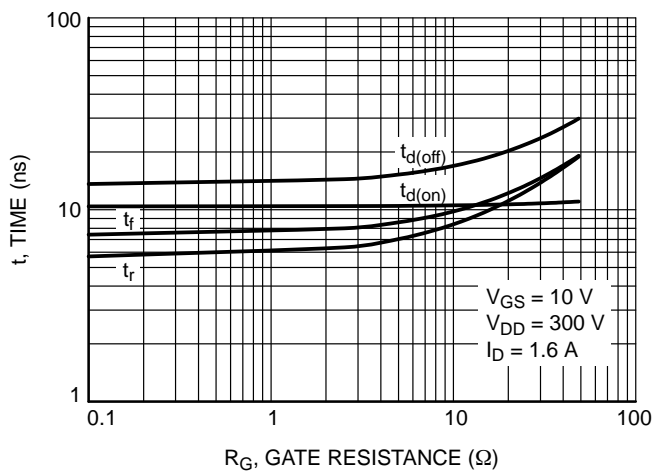


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

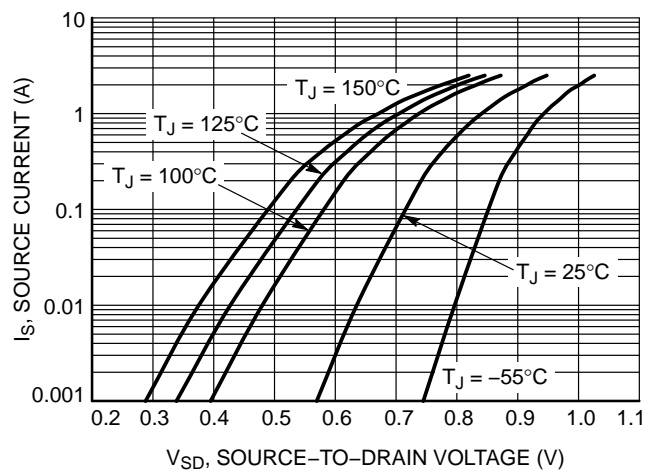


Figure 12. Diode Forward Voltage vs. Current

NDT02N60Z

TYPICAL CHARACTERISTICS

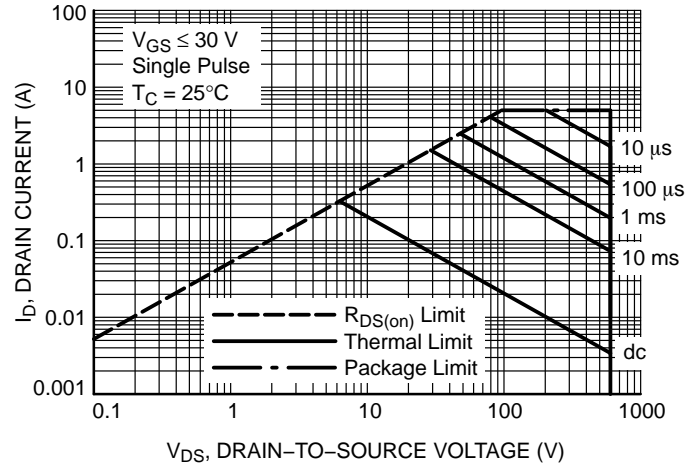


Figure 13. Maximum Rated Forward Biased Safe Operating Area

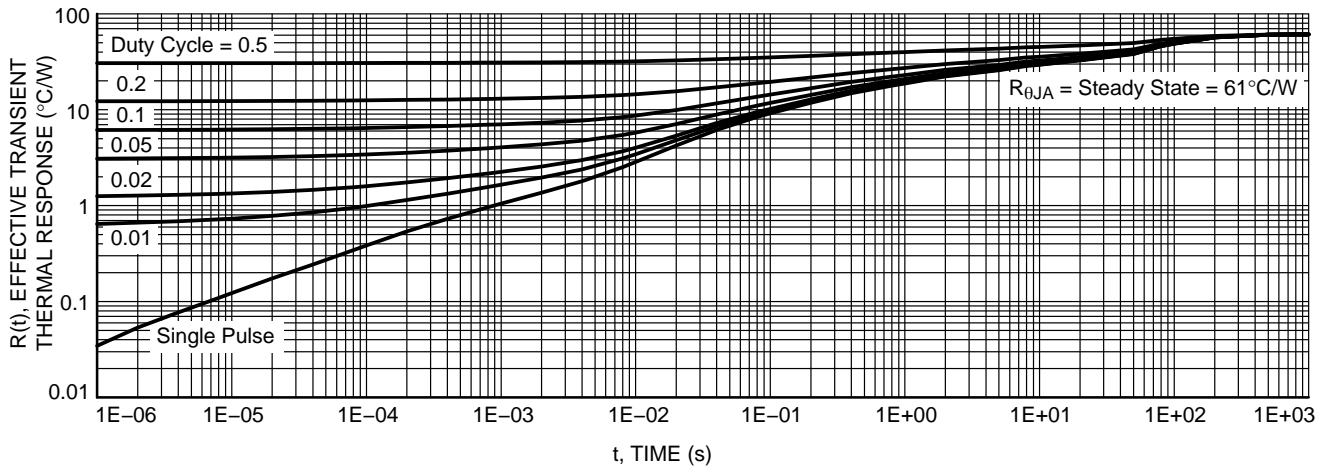


Figure 14. Thermal Impedance (Junction-to-Ambient)

ORDERING INFORMATION

Device	Package	Shipping†
NDT02N60ZT1G	SOT-223 (Pb-Free, Halogen Free)	1000 / Tape & Reel
NDT02N60ZT3G		4000 / Tape & Reel

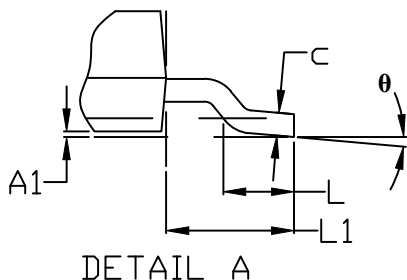
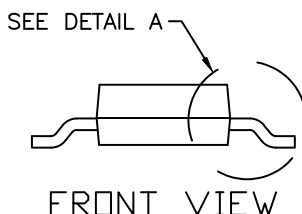
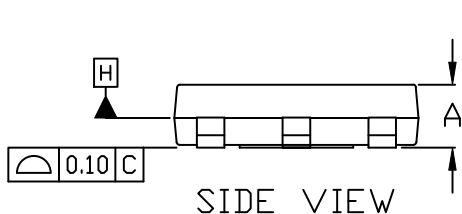
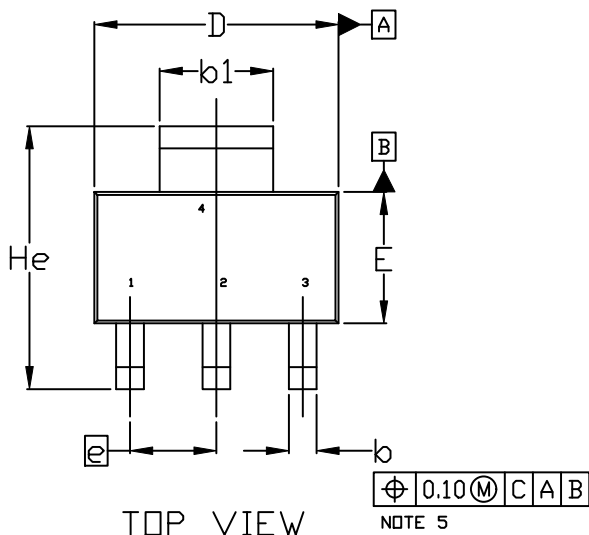
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SCALE 1:1

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

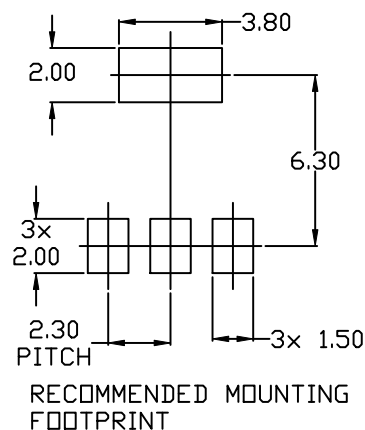
DATE 02 OCT 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°



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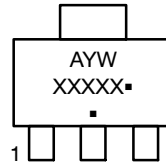
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SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		


**GENERIC
MARKING DIAGRAM***



A = Assembly Location
 Y = Year
 W = Work Week
 XXXXX = Specific Device Code
 ■ = Pb-Free Package

(Note: Microdot may be in either location)
 *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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